

| | |
|-------------------------|--|
| 1. Record Nr. | UNINA9910458827303321 |
| Titolo | Electroceramics [[electronic resource]] : production, properties and microstructures // edited by W.E. Lee and A. Bell |
| Pubbl/distr/stampa | London, : Institute of Materials, 1994 |
| ISBN | 1-907625-56-9 |
| Descrizione fisica | 1 online resource (354 p.) |
| Collana | British ceramic proceedings, , 0268-4373 ; ; no. 52 Book ; ; 564 |
| Altri autori (Persone) | LeeW. E Bella |
| Disciplina | 620.1404297 |
| Soggetti | Electronic ceramics Ceramic materials Electronic books. |
| Lingua di pubblicazione | Inglese |
| Formato | Materiale a stampa |
| Livello bibliografico | Monografia |
| Note generali | Symposium held in conjunction with Condensed Matter and Materials Physics Conference, 20-23 December 1993, University of Leeds. |
| Nota di bibliografia | Includes bibliographical references and indexes. |
| Nota di contenuto | Contents; Introductory Statement; The Influence of Crystal Chemistry on the Ferroelectric and Piezoelectric Properties of Perovskite Ceramics; Influence of Structural Defects on Properties of Zirconium Titanate Based Microwave Ceramics; Simulation of the Dielectric Function of Pb (Mg ^{1/3} Nb ^{2/3})O ₃ from the Superparaelectric Model; Chemical Synthesis and Processing of Bismuth Titanate (Bi ₄ Ti ₃ O ₁₂)Electroceramics in Thin-Layer Form by a Sol-Gel Method; Sol-Gel Ferroelectric PZT Thin Films for Non-Volatile Memory Applications Effect of Thermal Processing Conditions on the Structure and Properties of Sol-Gel Derived PZT Thin LayersFerroelectric Thin Films for Integrated Device Applications; Sol-Gel Derived PLZT Thin Layers Crystallised with Epitaxy on Surface-Modified Platinum Electrodes; Thin Films of PZT and Ca-Pt Prepared by a Sol-Gel Method; Aqueous and Sol-Gel Synthesis of Submicron PZT Materials and Development of Tape Casting Systems for Multilayer Actuator Fabrication; Dielectric Properties and Ageing of Fe-doped PZT Ceramics Prepared by the EDTA-Gel Method Preparation of PLZT Powder by a Citrate Gel TechniqueCitrate Gel Route Processing of ZnO Varistors; Suppression of Zinc Interstitial Ion |

Migration in ZnO Due to the Presence of Sodium Ions; Dielectric Properties of A and B Site Substituted Lead Magnesium Niobate; The Effect of Hot Isostatic Pressing on the Microstructure of Hydrothermally Processed PbTiO₃ Ceramics; Hot Isostatic Pressing of Aurivillius Compounds for High-Temperature Device Applications; Investigation of High-Temperature Piezoelectric Ceramics; 0-3 Piezoceramic-Thermoplastic Polymer Composites
The Morphology of Barium Titanate Powders Produced by the Barium Carbonate-Titanium Dioxide Reaction; Aqueous Processing of Barium Titanate Powders; The Effect of ZnO Additions on the Structure and Properties of Sr₂Nb₂O₇ Ceramics; Structural and Electrical Characterisation of a New Bismuth Vanadium Oxide; Structure and Electrical Properties of Ceria Based Oxide Ion Conductors Prepared at Low Temperatures; Development and Evaluation of Oxide Cathodes for Ceramic Fuel Cell Operation at Intermediate Temperatures
Hydrothermal Synthesis of Strontium Hexaferrite: Powder Composition, Morphology and Magnetic Properties; Properties of Reaction Sintered Manganese-Zinc Ferrites; Electrically Conducting Composite Ceramics Produced by Hydrothermal Synthesis; Glass-Ceramic Coatings for Stainless Steel; The Use of Nonlinear Ferroelectric Ceramic Dielectrics in High-Voltage Pulsed Power; D.C. Pre-Breakdown Photon Emission from an Alumina Insulator in Vacuum; Monitoring the Integrity of MOS Gate Oxides; Index; Author Index

Sommario/riassunto

Proceedings of the Symposium held as part of the Condensed Matter and Materials Conference in 1993. Contents include: ferroelectric thin films for integrated device applications; effect of thermal processing conditions on the structure and properties of sol-gel derived PZT thin layers; citrate gel-route processing of ZnO varistors; development and evaluation of oxide cathodes for ceramic fuel cell operation at intermediate temperatures; monitoring the integrity of MOS gate oxides.
